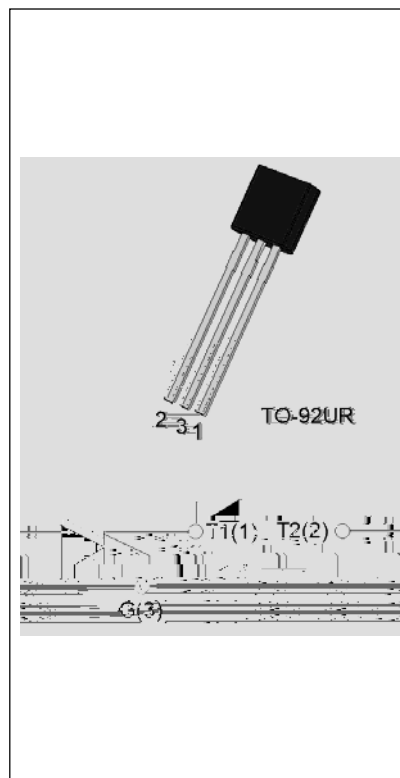




The JST01UR-1000SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST01UR-1000SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. Package TO-92UR is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	1000	V
$I_{GT} / /$	10/10/10	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	1000	V
RMS on-state current ($T_C \leq 45^\circ C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	15	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		16.5	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	1.25	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	1	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.1	W

Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	20	mA
				40	
I_H	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125$		MIN.	200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$ $T_j=125$		MIN.	1	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.4A$ $t_p=380\mu s$	$T_j=25$	1.3	V
V_{TO}	Threshold voltage	$T_j=125$	0.93	V
R_D	Dynamic resistance	$T_j=125$	146	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	8	μA
I_{RRM}		$T_j=125$	0.2	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	65	/W
$R_{th(j-a)}$	junction to ambient (AC)	150	/W

FIG.1: Maximum power dissipation versus RMS on-state current

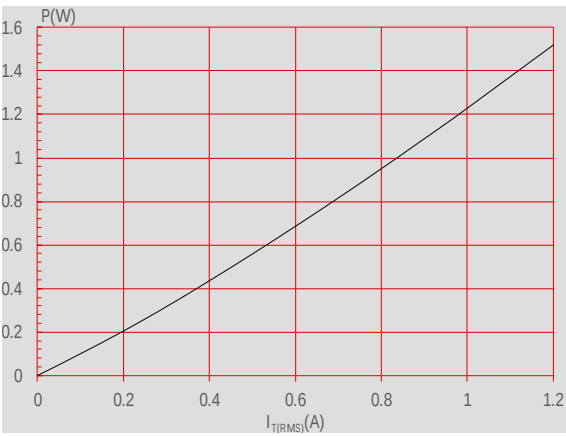


FIG.2: RMS on-state current versus case temperature

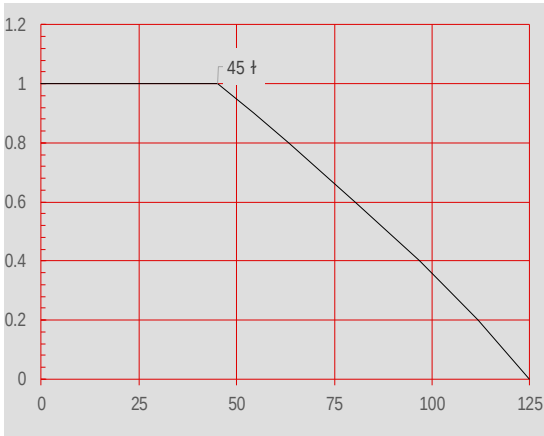
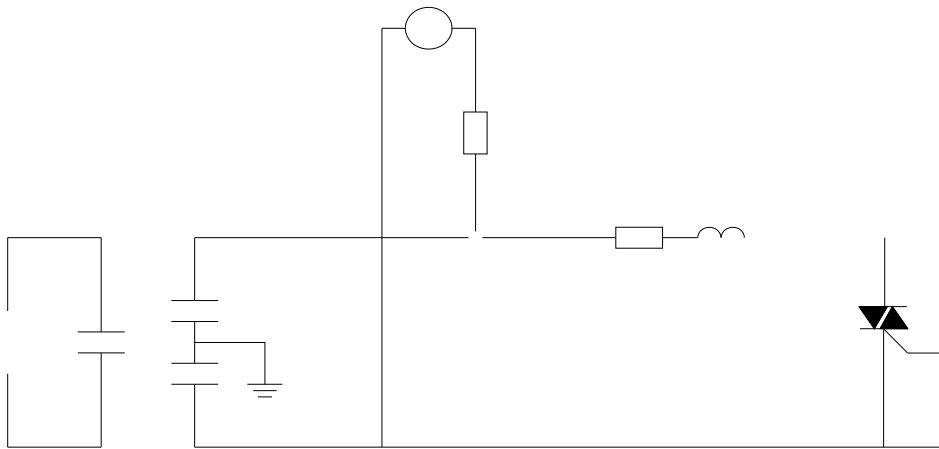
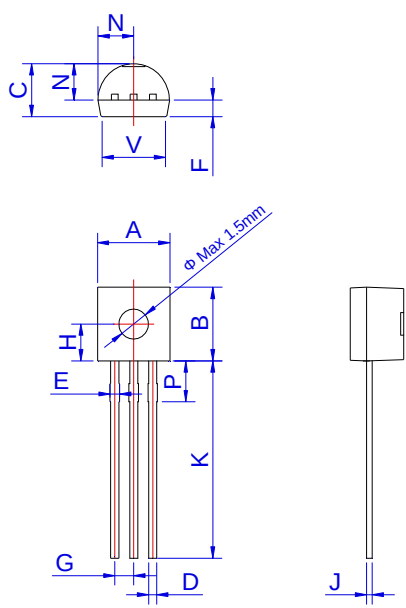


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards







Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	1.10		1.30			0.051
G	1.10		1.40	0.043		0.055
H	2.20		2.40	0.087		0.094
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.80		2.30	0.071		0.091
V	4.10		4.50	0.161		0.177



PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92UR	Bulk Pack	1,000	10,000	50,000

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
P	12.40	12.70	13.00	0.488	0.500	0.512
P0	12.40	12.70	13.00	0.488	0.500	0.512
P1	3.55	3.85	4.15	0.140	0.152	0.163
P2	5.95	6.35	6.75	0.233	0.250	0.265
P	-1.00	0	1.00	-0.039	0	0.039
F1 F2	2.30	2.50	2.70	0.090	0.098	0.106
F1-F2	-0.10	0	0.10	-0.004	0	0.004
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.50	6.00	6.50	0.217	0.236	0.256
W1	8.50	9.00	9.50	0.335	0.354	0.374
W2			1.00			0.039
D0	3.80	4.00	4.20	0.150	0.157	0.165
H	-1.00	0	1.00	-0.039	0	0.039
L1	2.50			0.098		
H	18.00	19.00	20.00	0.709	0.748	0.787

п
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